FUXINSEMI
INNOVATOR IN SEMICONDUCTOR

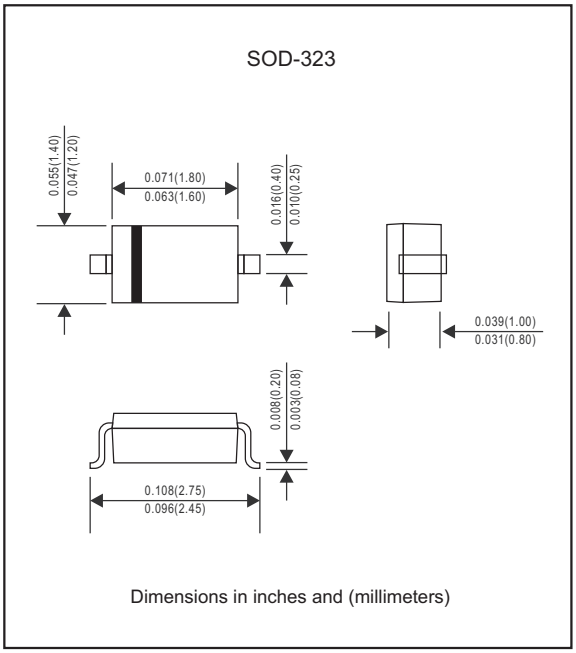
1N4148WX

200mW Surface Mount Switching Diode-100V

Features

- Fast switching speed.
- Electrically identical to standard JEDEC.
- Surface mount package ideally suited for automatic insertion.
- Tiny plastic SMD package.
- RoHS Compliant
- Compliant to Halogen-free
- High Conductance.
- Silicon epitaxial planar chip.
- Lead-free parts for green partner, exceeds environmental standards of MIL-STD-19500 /228

Package Outline



Mechanical data

- Epoxy : UL94-V0 rated flame retardant
- Case : Molded plastic, SOD-323
- Terminals :Plated terminals, solderable per MIL-STD-750, Method 2026
- Polarity : Indicated by cathode band
- Mounting Position : Any

Maximum ratings and Electrical Characteristics (AT T_A=25°C unless otherwise noted)

PARAMETER	Symbol	1N4148WX	UNIT
Maximum reverse voltage	V_R	75	V
Maximum peak reverse voltage	V_{RM}	100	V
Maximum RMS voltage	V_{RMS}	50	V
Maximum DC blocking voltage	V_{DC}	75	V
Maximum average forward current at T_A = 25°C	I_O	200	mA
Maximum peak forward surge current, 1.0us	I_{FSM}	2.0	A
Maximum power dissipation derate above 25°C	P_D	200	mW
Maximum forward voltage	V_F	0.715@IF=0.001A 0.855@IF=0.01A 1.0@IF=0.05A 1.25@IF=0.15A	V
Maximum DC reverse current at rated DC blocking voltage T_J = 25°C	I_R	0.025@VR=20V 1.0@VR=75V	uA
Typical junction capacitance (Notes 1)	C_J	2.0	pF
Maximum reverse recovery time (Notes 2)	t_{rr}	4.0	ns
Typical thermal resistance junction to ambient	$R_{\theta JA}$	500	°C/W
Operating junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes :
1. C_J at V_R = 0V, f = 1MHZ
2. From I_F = 10mA to I_R = 1mA, V_R = 6V, R_L = 100ohm

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Rating and characteristic curves

Fig. 1 TYPICAL FORWARD CHARACTERISTICS

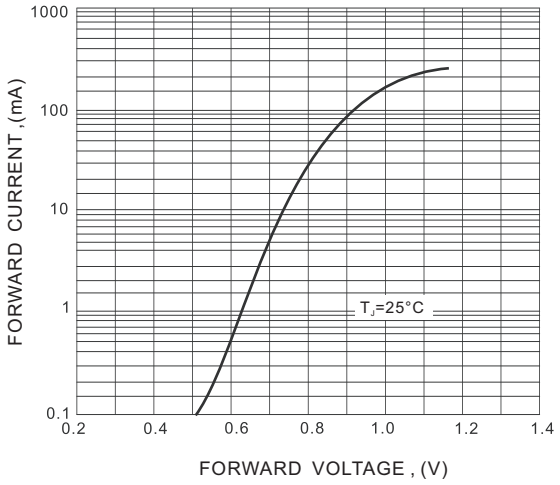


Fig. 2 TYPICAL REVERSE CHARACTERISTICS

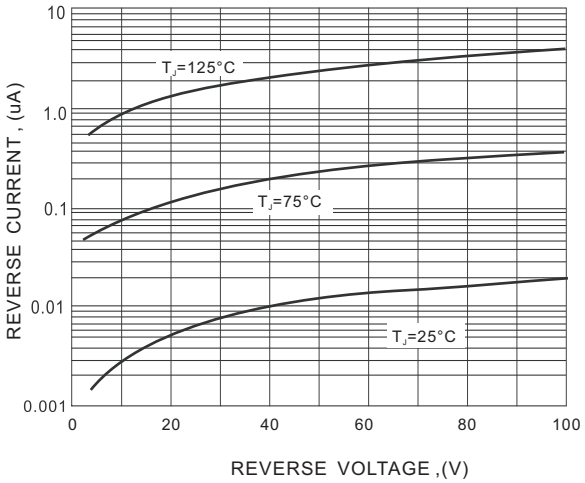
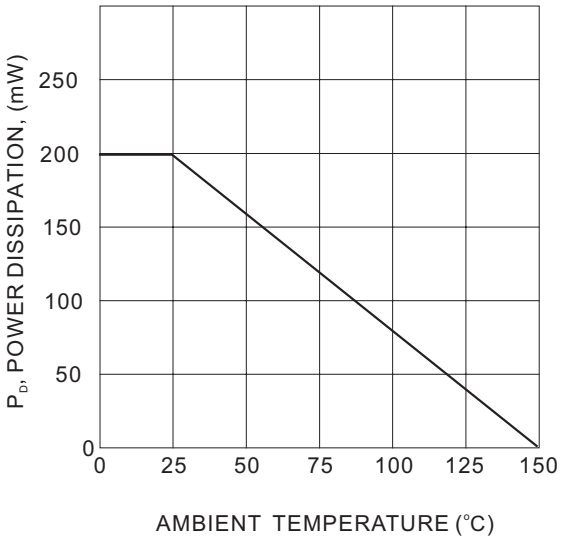


Fig. 3 POWER DERATING CURVE



Marking

Type number	Marking code
1N4148WX	T4